

SEB551V-30
Schottky barrier diode

Revision:A

Features

- Small mold type. (UMD2)
- Low VF
- High reliability

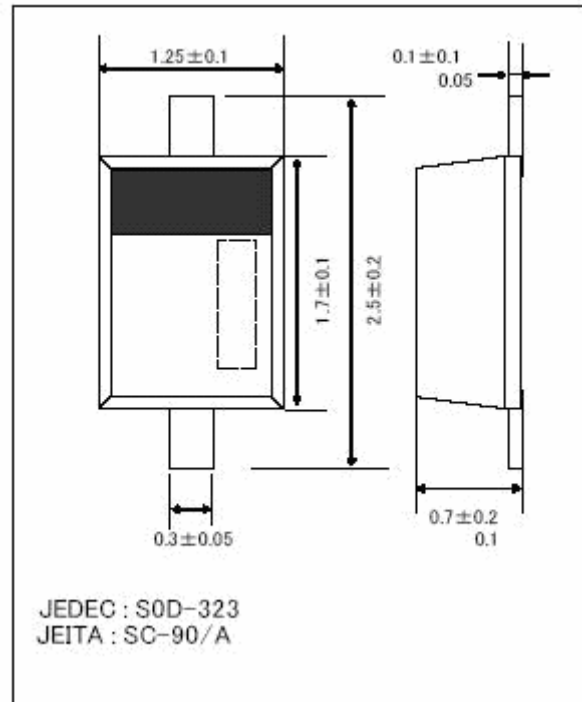
Applications

- High frequency rectification

Construction

- Silicon epitaxial planar

● External dimensions (Unit : mm)



Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
DC reverse voltage	V_R	20	V
Average rectified forward current	I_O	500	mA
Forward peak surge current (60Hz 1cyc.)	I_{FSM}	2	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

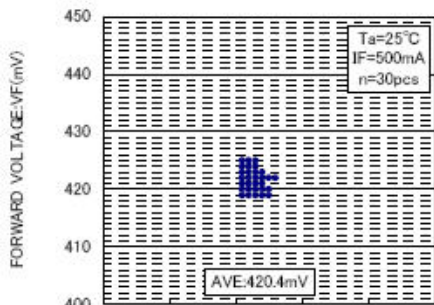
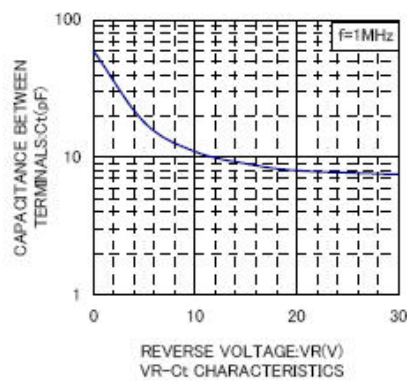
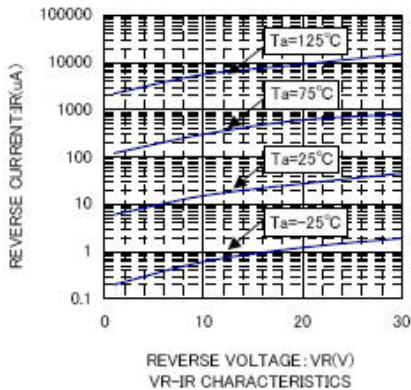
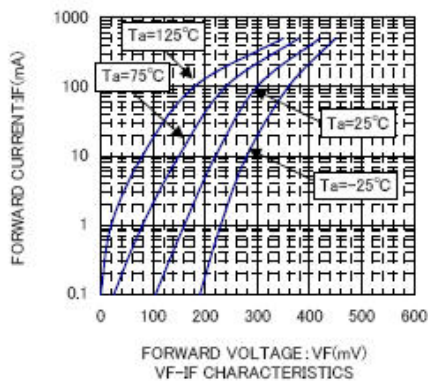
* 60Hz, 1ms

Electrical characteristics (Ta=25°C)

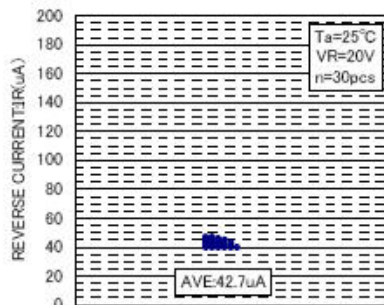
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	—	0.36	V	$I_F = 100mA$
	V_{F2}	—	—	0.47	V	$I_F = 500mA$
Reverse current	I_R	—	—	100	uA	$V_R = 20V$

- Please pay attention to static electricity when handling.

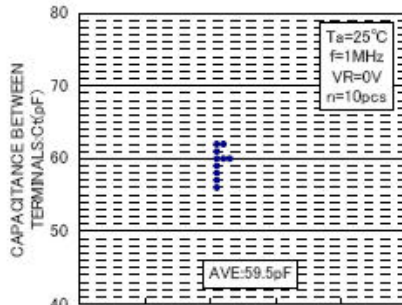
●Electrical characteristic curves (Ta = 25°C)



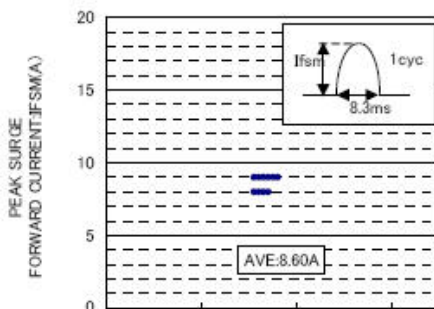
VF DISPERSION MAP



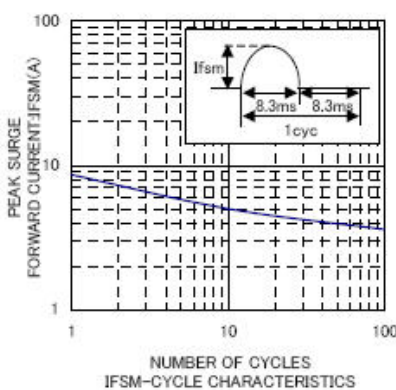
IR DISPERSION MAP



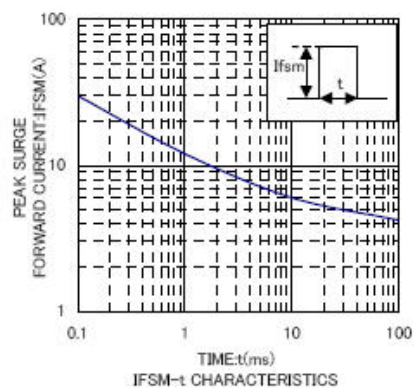
Ct DISPERSION MAP



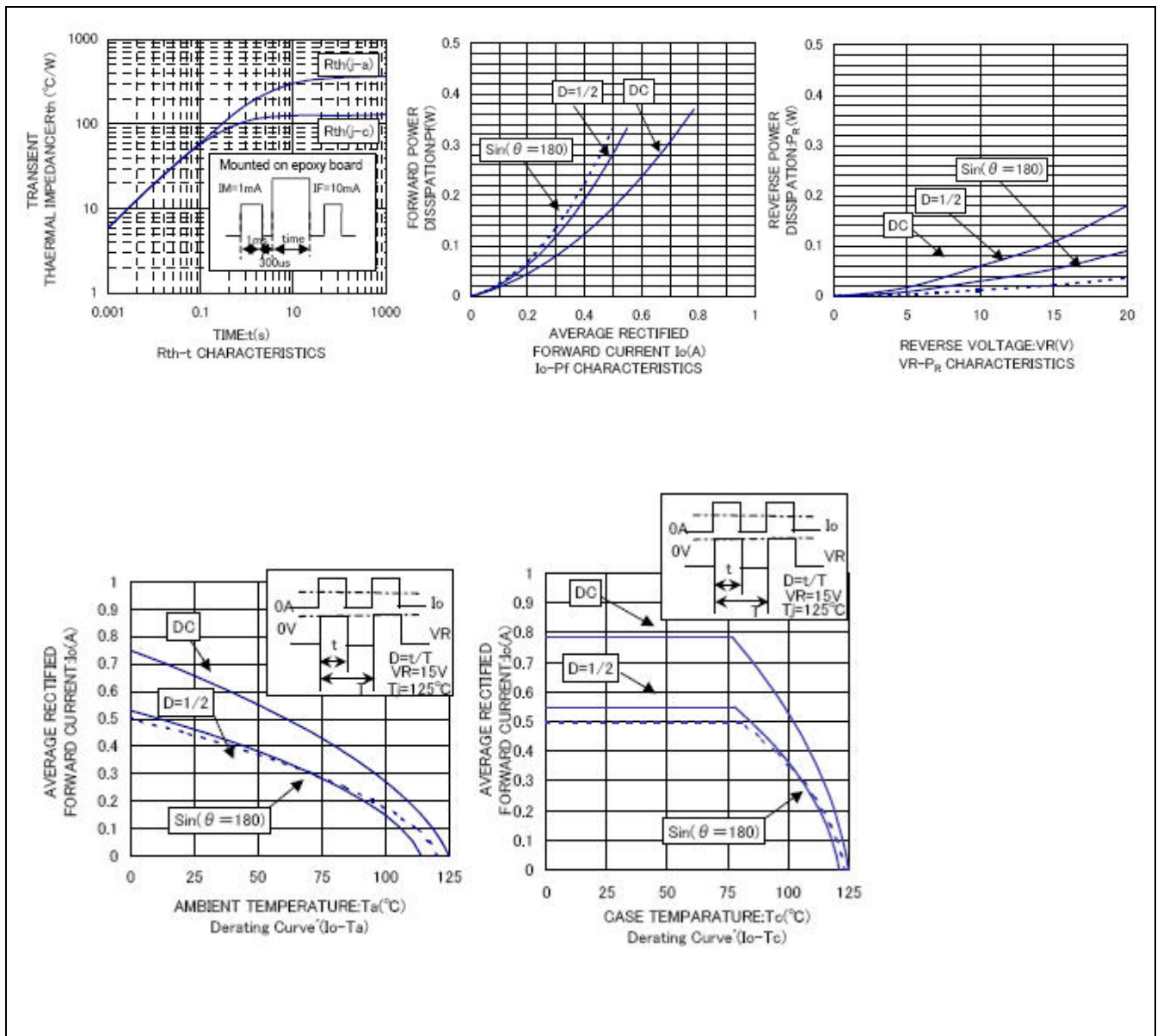
IFSM DISPERSION MAP



IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS



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